# PBSS5240X

# 40 V, 2 A PNP low VCEsat (BISS) transistor

19 October 2012

**Product data sheet** 

## 1. Product profile

#### 1.1 General description

PNP low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a medium power and flat lead SOT89 Surface-Mounted Device (SMD) plastic package. NPN complement: PBSS4240X.

#### 1.2 Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- · High efficiency due to less heat generation

### 1.3 Applications

- DC-to-DC conversion
- Supply line switching
- Battery charger
- LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)
- Inductive load driver (e.g. relays, buzzers and motors)

## 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-40	V
I <sub>C</sub>	collector current		-	-	-2	Α
I <sub>CM</sub>	peak collector current		-	-	-3	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -1 A; $I_B$ = -100 mA; pulsed; $t_p$ ≤ 300 μs; $\delta$ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	-	310	mΩ
I <sub>CRM</sub>	repetitive peak collector current	$t_p \le 20 \text{ ms}; \ \delta \le 0.33 \ ; \ \text{pulsed}$	-	-	-2.5	А





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# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter		C
2	С	collector		в—
3	В	base	3 2 1	E sym132
			SOT89	5,111.02

# 3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBSS5240X	SOT89	plastic surface-mounted package; die pad for good heat transfer; 3 leads	SOT89			

# 4. Marking

Table 4. Marking codes

3	
Type number	Marking code
PBSS5240X	S48

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-40	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-40	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-5	V
I <sub>C</sub>	collector current			-	-2	Α
I <sub>CRM</sub>	repetitive peak collector current	$\delta \le 0.33$ ; $t_p \le 20$ ms; pulsed		-	-2.5	Α
I <sub>CM</sub>	peak collector current			-	-3	Α
I <sub>B</sub>	base current			-	-300	mA
I <sub>BM</sub>	peak base current			-	-1	Α
P <sub>tot</sub>	total power dissipation		[1]	-	0.5	W
			[2]	-	0.95	W

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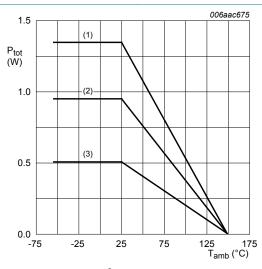
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### 40 V, 2 A PNP low VCEsat (BISS) transistor

Symbol	Parameter	Conditions		Min	Max	Unit
			[3]	-	1.35	W
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



- (1) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (2) FR4 PCB, mounting pad for collector 1 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

## 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient		in free air	[1]	-	-	250	K/W
			[2]	-	-	132	K/W
	ambient		[3]	-	-	93	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	16	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

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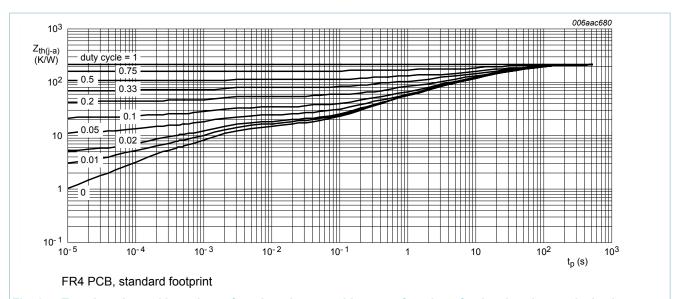


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

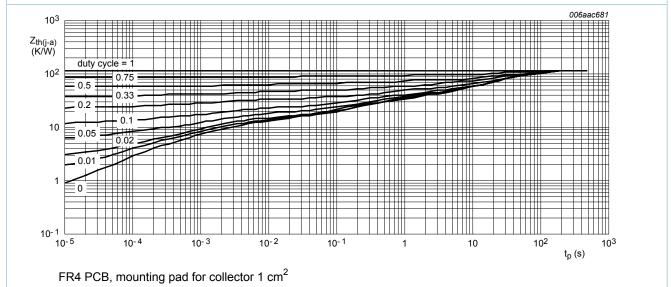
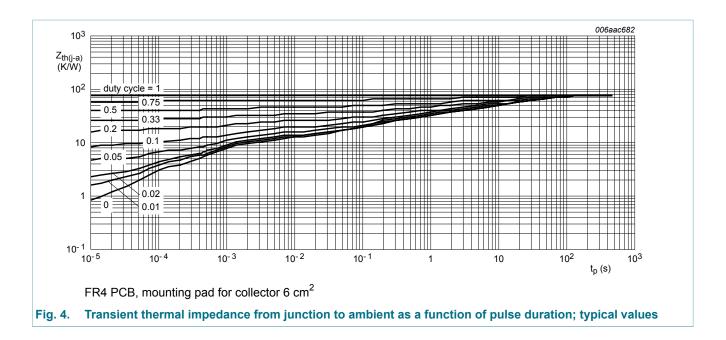


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 7. Characteristics

Table 7. Characteristics

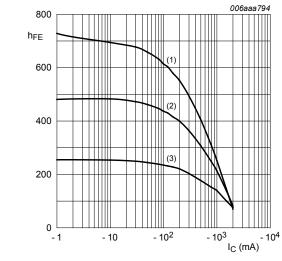
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB} = -40 \text{ V}; I_E = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
	current	$V_{CB}$ = -40 V; $I_{E}$ = 0 A; $T_{j}$ = 150 °C	-	-	-50	μA
I <sub>CEO</sub>	collector-emitter cut-off current	V <sub>CE</sub> = -30 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -5 V; $I_{C}$ = -1 mA; $T_{amb}$ = 25 °C	300	-	-	
		$V_{CE}$ = -5 V; $I_{C}$ = -500 mA; $T_{amb}$ = 25 °C	215	-	-	
		$V_{CE}$ = -5 V; $I_{C}$ = -1 A; $T_{amb}$ = 25 °C	145	-	-	
		$V_{CE}$ = -5 V; $I_{C}$ = -2 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	55	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = -100 mA; $I_B$ = -5 mA; $T_{amb}$ = 25 °C	-	-	-140	mV
		I <sub>C</sub> = -500 mA; I <sub>B</sub> = -50 mA; T <sub>amb</sub> = 25 °C	-	-	-170	mV
		$I_C$ = -1 A; $I_B$ = -100 mA; pulsed; $t_p \le 300 \ \mu s$ ; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	-	-310	mV
		$I_C$ = -2 A; $I_B$ = -200 mA; pulsed; $t_p \le 300 \ \mu s$ ; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	-	-630	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C}$ = -1 A; $I_{B}$ = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; \ T_{amb}$ = 25 °C	-	-	310	mΩ

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### 40 V, 2 A PNP low VCEsat (BISS) transistor

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = -1 A; $I_B$ = -100 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-	-1.2	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$V_{CE} = -5 \text{ V; } I_{C} = -1 \text{ A; pulsed;}$ $t_{p} \le 300 \text{ µs; } \delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	-	-	-1.1	V
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; $I_{C}$ = -50 mA; f = 100 MHz; $T_{amb}$ = 25 °C	150	-	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB}$ = -10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C	-	-	12	pF



 $V_{CE} = -5 V$ 

(1)  $T_{amb}$  = 100 °C

(2)  $T_{amb}$  = 25 °C

(3)  $T_{amb} = -55 \,^{\circ}C$ 

Fig. 5. DC current gain as a function of collector current; typical values

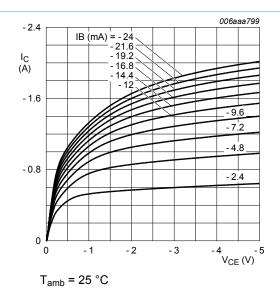
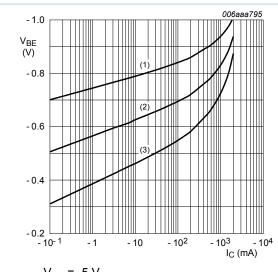


Fig. 6. Collector current as a function of collectoremitter voltage; typical values

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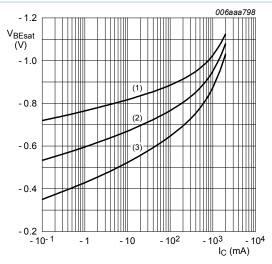
$$V_{CE}$$
 = -5  $V$ 

(1) 
$$T_{amb} = -55$$
 °C

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter voltage as a function of collector current; typical values



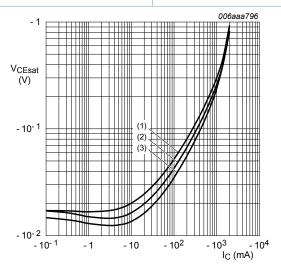
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = -55$$
 °C

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

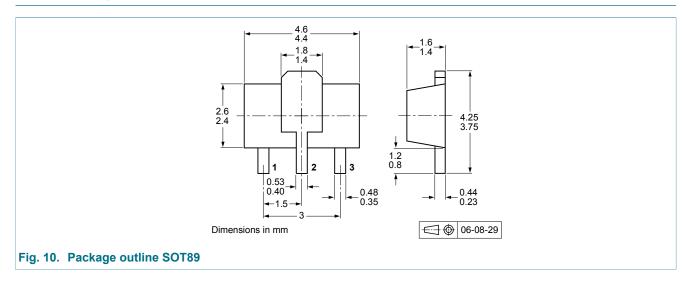
(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

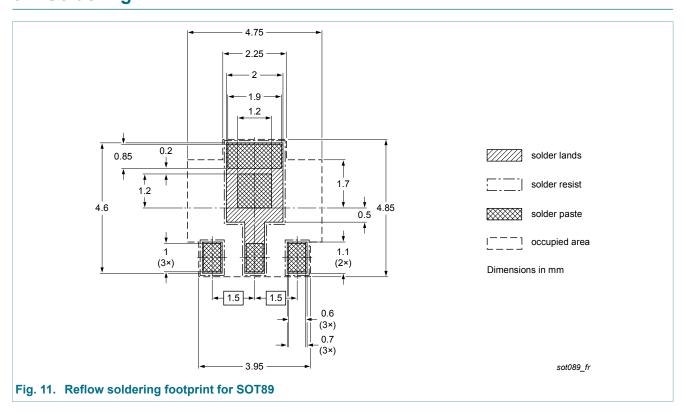
Collector-emitter saturation voltage as a function of collector current; typical values Fig. 9.

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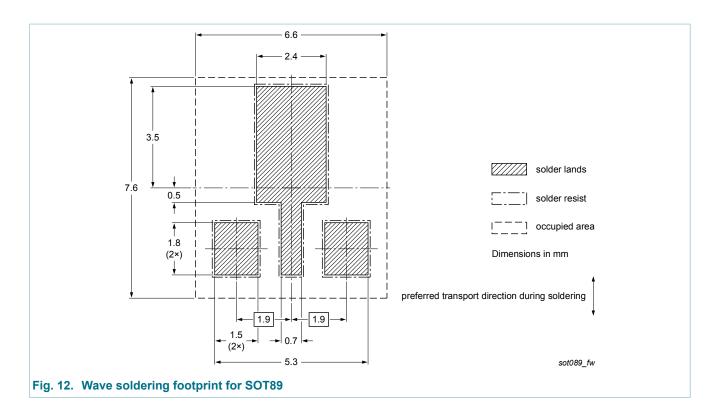
## 8. Package outline



## 9. Soldering



## 40 V, 2 A PNP low VCEsat (BISS) transistor



# 10. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5240X v.1	20121019	Product data sheet	-	-

#### 40 V, 2 A PNP low VCEsat (BISS) transistor

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